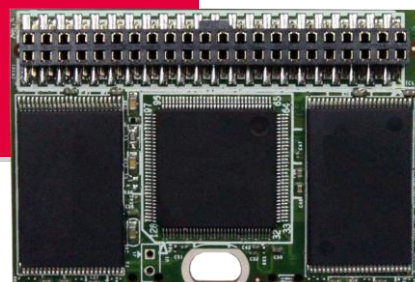


Datasheet

EDC 1ME series

- iSMART disk health monitoring
- Intelligent error recovery system
- Excellent data transfer speed
- Write protection security
- Enhanced power cycling management



Introduction

The Innodisk Embedded DISK CARD 1ME (EDC 1ME) products provide high capacity solid-state flash memory that electrically complies with the Personal Computer Memory Card International Association ATA standard. Innodisk Embedded DISK CARD 1ME (EDC 1ME) is embedded solid-state data storage systems for industrial work place. Embedded DISK CARD 1ME (EDC 1ME) features an extremely light weight, reliable, low-profile form factor.

Embedded DISK CARD 1ME (EDC 1ME) supports advanced PIO (0-6), Multi Word DMA (0-4), Ultra DMA (0-6) transfer modes, multi-sector transfers, and LBA addressing

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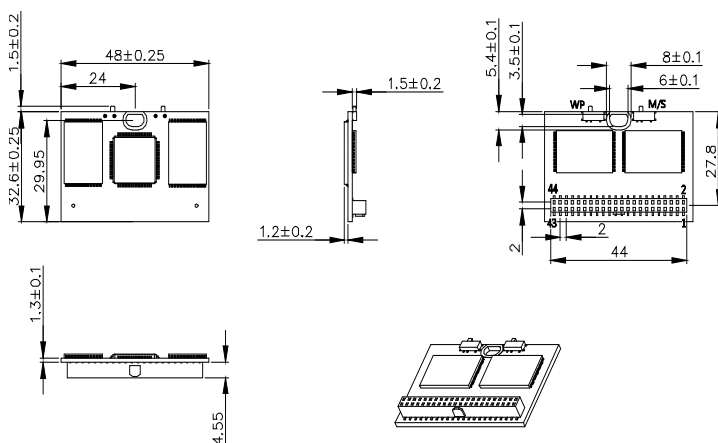
(ES) Equipements Scientifiques SA - Département Modules & Systèmes Informatiques - 127 rue de Buzenval BP 26 - 92380 Garches
Tél. 01 47 95 99 80 - Fax. 01 47 01 16 22 - e-mail: msi@es-france.com - Site Web: www.es-france.com

**Contact us for more information
about the EDC 1ME**

Innodisk is a service-driven provider of industrial embedded flash and DRAM storage products and technologies, with a focus on the cloud computing, industrial/embedded, and aerospace and defense industries.

EDC 1ME series

Drawing



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20150413

Specifications

Interface	PATA
Flash Type	MLC
Capacity	8GB~256GB
Max. Channels	2
Sequential R/W (MB/sec, max.)	110/75
Max. Power Consumption	0.76W(3.3V x 230mA)
Thermal Sensor	-
External DRAM Buffer	-
H/W Write Protect	Optional
ATA Security	✓
S.M.A.R.T.	✓
Dimension (WxLxH)	48X 32.6 X 7.3 mm
Environment	Vibration: 20G @7~2000Hz Shock: 1500G @ 0.5ms Storage Temperature: -55°C ~ +95°C MTBF: 3 million hours

Ordering Information

Operation Temp.	8GB	16GB	32GB	64GB	128GB	256GB
Standard Grade (0°C ~ +70°C)	DEE4X-08GD53RC1SC DEE4X-08GD53BC1SC	DEE4X-16GD53RC1DC DEE4X-16GD53BC1SC	DEE4X-32GD53RC1DC DEE4X-32GD53BC1DC	DEE4X-64GD53RC1DC DEE4X-64GD53BC1DC	DEE4X-A28D53RC1DC DEE4X-A28D53BC1DC	DEE4X-B56D53BC1DC
Industrial Grade (-40°C ~ +85°C)	DEE4X-08GD53RW1SC DEE4X-08GD53BW1SC	DEE4X-16GD53RW1DC DEE4X-16GD53BW1DC	DEE4X-32GD53RW1DC DEE4X-32GD53BW1DC	DEE4X-64GD53RW1DC DEE4X-64GD53BW1DC	DEE4X-A28D53RC1DC DEE4X-A28D53BW1DC	DEE4X-B56D53BW1DC

R: Toshiba A19nm MLC / B: Toshiba 15nm MLC
X= A~B; connector type



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